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The invention relates to the semiconductor technology and may be used in the electronics and power engineering.

The process for polysulphide film obtaining includes treatment of the compounds $Zn_xIn_2S_{3+x}$ (x=1, 2, 3, 5) with $ZnCl_2$ solution, deposition onto a support, preliminarily treated in $ZnCl_2$ solution, with subsequent drying at the temperature of 373 K and thermal treatment at T×t $(6,3–8,5)10^3$ degree × hour (where T and t –temperature and treatment time respectively).

Claims: 1